

Fang-Fang Ren

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

127
papers

1,875
citations

23
h-index

38
g-index

134
ext. papers

2,433
ext. citations

3.8
avg. IF

5.04
L-index

#	Paper	IF	Citations
127	Majority and Minority Carrier Traps in NiO/AlGaInP-n Heterojunction Diode. <i>IEEE Transactions on Electron Devices</i> , 2022 , 1-7	2.9	1
126	1.2 kV/25 A Normally off P-N Junction/AlGaIn/GaN HEMTs With Nanosecond Switching Characteristics and Robust Overvoltage Capability. <i>IEEE Transactions on Power Electronics</i> , 2022 , 37, 26-30	7.2	3
125	70- μ m-Body Ga ₂ O ₃ Schottky Barrier Diode with 1.48 K/W Thermal Resistance, 59 A Surge Current and 98.9% Conversion Efficiency. <i>IEEE Electron Device Letters</i> , 2022 , 1-1	4.4	2
124	Dislocation dynamics in AlGaInO ₃ micropillars from selective-area epitaxy to epitaxial lateral overgrowth. <i>Applied Physics Letters</i> , 2022 , 120, 121601	3.4	1
123	M-Plane AlGaIn Solar-Blind Detector With Record-High Responsivity-Bandwidth Product and High-Temperature Operation Capability. <i>IEEE Electron Device Letters</i> , 2022 , 43, 541-544	4.4	2
122	Unlocking the Single-Domain Heteroepitaxy of Orthorhombic AlGaInO ₃ via Phase Engineering. <i>ACS Applied Electronic Materials</i> , 2022 , 4, 461-468	4	2
121	4H-SiC n-i-p extreme ultraviolet detector with gradient doping-induced surface junction. <i>IEEE Electron Device Letters</i> , 2022 , 1-1	4.4	0
120	Development of p-i-n radiation detectors based on semi-insulating 4H-SiC substrate via dual-face ion implantation. <i>Solid-State Electronics</i> , 2021 , 187, 108196	1.7	1
119	Strain-driven phase manipulation of Al and AlGaInO ₃ by nanoepitaxial lateral overgrowth on embedded In ₂ O ₃ submicron dots. <i>Applied Physics Letters</i> , 2021 , 119, 182102	3.4	1
118	Field-Plated NiO/Ga ₂ O ₃ p-n Heterojunction Power Diodes With High-Temperature Thermal Stability and Near Unity Ideality Factors. <i>IEEE Journal of the Electron Devices Society</i> , 2021 , 1-1	2.3	1
117	1000-W Resistive Energy Dissipating Capability Against Inductive Transients Demonstrated in Non-Avalanche AlGaIn/GaN Schottky Diode. <i>IEEE Electron Device Letters</i> , 2021 , 42, 1743-1746	4.4	0
116	A self-powered solar-blind photodetector based on polyaniline/AlGaInO ₃ p-n heterojunction. <i>Applied Physics Letters</i> , 2021 , 119, 141601	3.4	4
115	High sensitivity x-ray detectors based on 4H-SiC p-i-n structure with 80 μ m thick intrinsic layer. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2021 , 39, 022202	1.3	1
114	Vertical Field-Plated NiO/Ga ₂ O ₃ Heterojunction Power Diodes 2021 ,		1
113	High Performance Quasi-Vertical GaN Junction Barrier Schottky Diode with Zero Reverse Recovery and Rugged Avalanche Capability 2021 ,		4
112	AlGaInO ₃ vertical heterojunction barrier Schottky diodes terminated with p-NiO field limiting rings. <i>Applied Physics Letters</i> , 2021 , 118, 202102	3.4	14
111	In situ heteroepitaxial construction and transport properties of lattice-matched In ₂ O ₃ /AlGaInO ₃ p-n heterojunction. <i>Applied Physics Letters</i> , 2021 , 118, 261601	3.4	13

110	High-Voltage Quasi-Vertical GaN Junction Barrier Schottky Diode With Fast Switching Characteristics. <i>IEEE Electron Device Letters</i> , 2021 , 42, 974-977	4.4	13
109	Demonstration of Avalanche and Surge Current Robustness in GaN Junction Barrier Schottky Diode With 600-V/10-A Switching Capability. <i>IEEE Transactions on Power Electronics</i> , 2021 , 36, 12163-12167	7.2	6
108	1.37 kV/12 A NiO/EGa2O3 Heterojunction Diode With Nanosecond Reverse Recovery and Rugged Surge-Current Capability. <i>IEEE Transactions on Power Electronics</i> , 2021 , 36, 12213-12217	7.2	19
107	Band Alignment and Enhanced Interfacial Conductivity Manipulated by Polarization in a Surfactant-Mediated Grown EGa2O3/In2O3 Heterostructure. <i>ACS Applied Electronic Materials</i> , 2021 , 3, 795-803	4	2
106	Over 1.8 GW/cm ² beveled-mesa NiO/EGa2O3 heterojunction diode with 800 V/10 A nanosecond switching capability. <i>Applied Physics Letters</i> , 2021 , 119, 262103	3.4	1
105	Effect of a Single Threading Dislocation on Electrical and Single Photon Detection Characteristics of 4H-SiC Ultraviolet Avalanche Photodiodes. <i>Chinese Physics Letters</i> , 2020 , 37, 068502	1.8	1
104	Misfit epitaxial strain manipulated transport properties in cubic In2O3 hetero-epilayers. <i>Applied Physics Letters</i> , 2020 , 117, 102104	3.4	1
103	High-Performance 4H-SiC Schottky Photodiode With Semitransparent Grid-Electrode for EUV Detection. <i>IEEE Photonics Technology Letters</i> , 2020 , 32, 791-794	2.2	4
102	. <i>IEEE Electron Device Letters</i> , 2020 , 1-1	4.4	13
101	After-Pulse Characterizations of Geiger-Mode 4H-SiC Avalanche Photodiodes. <i>IEEE Photonics Technology Letters</i> , 2020 , 32, 706-709	2.2	1
100	Polarization-Independent Indium Phosphide Nanowire Photodetectors. <i>Advanced Optical Materials</i> , 2020 , 8, 2000514	8.1	3
99	Band Alignment and Interface Recombination in NiO/EGa2O3 Type-II p-n Heterojunctions. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 3341-3347	2.9	24
98	Phase tailoring and wafer-scale uniform hetero-epitaxy of metastable-phased corundum EGa2O3 on sapphire. <i>Applied Surface Science</i> , 2020 , 513, 145871	6.7	16
97	Anion Engineering Enhanced Response Speed and Tunable Spectral Responsivity in Gallium-Oxynitrides-Based Ultraviolet Photodetectors. <i>ACS Applied Electronic Materials</i> , 2020 , 2, 808-816	6	6
96	Highly Enhanced Inductive Current Sustaining Capability and Avalanche Ruggedness in GaN p-i-n Diodes With Shallow Bevel Termination. <i>IEEE Electron Device Letters</i> , 2020 , 41, 469-472	4.4	7
95	Hybrid Light Emitters and UV Solar-Blind Avalanche Photodiodes based on III-Nitride Semiconductors. <i>Advanced Materials</i> , 2020 , 32, e1904354	24	11
94	Property manipulation through pulsed laser annealing in high dose Mg-implanted GaN. <i>Journal of Applied Physics</i> , 2020 , 128, 235704	2.5	1
93	High- HfO_2 -Based AlGaIn/GaN MIS-HEMTs With Y2O3 Interfacial Layer for High Gate Controllability and Interface Quality. <i>IEEE Journal of the Electron Devices Society</i> , 2020 , 8, 15-19	2.3	7

92	Gallium oxide-based solar-blind ultraviolet photodetectors. <i>Semiconductor Science and Technology</i> , 2020 , 35, 023001	1.8	40
91	Electron-Beam-Driven III-Nitride Plasmonic Nanolasers in the Deep-UV and Visible Region. <i>Small</i> , 2020 , 16, e1906205	11	9
90	A 1.86-kV double-layered NiO/AlGa ₂ O ₃ vertical p-n heterojunction diode. <i>Applied Physics Letters</i> , 2020 , 117, 022104	3.4	58
89	Si-based Multiband Terahertz Antennas 2019 ,		1
88	Highly Narrow-Band Polarization-Sensitive Solar-Blind Photodetectors Based on AlGaO Single Crystals. <i>ACS Applied Materials & Interfaces</i> , 2019 , 11, 7131-7137	9.5	38
87	Realization of p-type gallium nitride by magnesium ion implantation for vertical power devices. <i>Scientific Reports</i> , 2019 , 9, 8796	4.9	18
86	Gate-first process compatible, high-quality in situ SiN _x for surface passivation and gate dielectrics in AlGaIn/GaN MISHEMTs. <i>Journal Physics D: Applied Physics</i> , 2019 , 52, 305105	3	4
85	. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 2276-2281	2.9	33
84	Investigation and active suppression of self-heating induced degradation in amorphous InGaZnO thin film transistors. <i>Chinese Physics B</i> , 2019 , 28, 017303	1.2	1
83	Transition of photoconductive and photovoltaic operation modes in amorphous Ga ₂ O ₃ -based solar-blind detectors tuned by oxygen vacancies. <i>Chinese Physics B</i> , 2019 , 28, 028501	1.2	13
82	Spatial Non-Uniform Hot Carrier Luminescence From 4H-SiC p-i-n Avalanche Photodiodes. <i>IEEE Photonics Technology Letters</i> , 2019 , 31, 447-450	2.2	6
81	Performance improvement of 4H-SiC PIN ultraviolet avalanche photodiodes with different intrinsic layer thicknesses. <i>Chinese Physics B</i> , 2019 , 28, 098503	1.2	2
80	On the origin of dislocation generation and annihilation in AlGa ₂ O ₃ epilayers on sapphire. <i>Applied Physics Letters</i> , 2019 , 115, 182101	3.4	20
79	Investigations of the gate instability characteristics in Schottky/ohmic type p-GaN gate normally-off AlGaIn/GaN HEMTs. <i>Applied Physics Express</i> , 2019 , 12, 121005	2.4	3
78	Band alignment and band bending at AlGa ₂ O ₃ /ZnO n-n isotype hetero-interface. <i>Applied Physics Letters</i> , 2019 , 115, 202101	3.4	13
77	Effect of Very High-Fluence Proton Radiation on 6H-SiC Photoconductive Proton Detectors. <i>IEEE Electron Device Letters</i> , 2019 , 40, 1929-1932	4.4	6
76	Review of gallium-oxide-based solar-blind ultraviolet photodetectors. <i>Photonics Research</i> , 2019 , 7, 381	6	203
75	Magnesium ion-implantation-based gallium nitride p-i-n photodiode for visible-blind ultraviolet detection. <i>Photonics Research</i> , 2019 , 7, B48	6	20

74	Crosstalk Analysis of SiC Ultraviolet Single Photon Avalanche Photodiode Arrays. <i>IEEE Photonics Journal</i> , 2019 , 11, 1-8	1.8	4
73	Heteroepitaxial growth of thick β -Ga ₂ O ₃ film on sapphire (0001) by MIST-CVD technique. <i>Journal of Semiconductors</i> , 2019 , 40, 012804	2.3	24
72	Vertical 4H-SiC n-i-p-n APDs With Partial Trench Isolation. <i>IEEE Photonics Technology Letters</i> , 2018 , 30, 805-808	2.2	6
71	Identification and modulation of electronic band structures of single-phase β (Al _x Ga _{1-x}) ₂ O ₃ alloys grown by laser molecular beam epitaxy. <i>Applied Physics Letters</i> , 2018 , 113, 041901	3.4	29
70	Tailored Emission Properties of ZnTe/ZnTe:O/ZnO Core-Shell Nanowires Coupled with an Al Plasmonic Bowtie Antenna Array. <i>ACS Nano</i> , 2018 , 12, 7327-7334	16.7	7
69	Low-threshold ultraviolet stimulated emissions from large-sized single crystalline ZnO transferable membranes. <i>Optics Express</i> , 2018 , 26, 31965-31975	3.3	3
68	Vertically Emitting Indium Phosphide Nanowire Lasers. <i>Nano Letters</i> , 2018 , 18, 3414-3420	11.5	25
67	Avalanche Ruggedness of GaN p-i-n Diodes Grown on Sapphire Substrate. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018 , 215, 1800069	1.6	6
66	4H-SiC Ultraviolet Avalanche Photodiodes With Small Gain Slope and Enhanced Fill Factor. <i>IEEE Photonics Journal</i> , 2017 , 9, 1-8	1.8	7
65	Distinct enhancement of sub-bandgap photoresponse through intermediate band in high dose implanted ZnTe:O alloys. <i>Scientific Reports</i> , 2017 , 7, 44399	4.9	6
64	Solar-Blind Photodetector with High Avalanche Gains and Bias-Tunable Detecting Functionality Based on Metastable Phase β -GaO/ZnO Isotype Heterostructures. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 36997-37005	9.5	106
63	Extreme absorption enhancement in ZnTe:O/ZnO intermediate band core-shell nanowires by interplay of dielectric resonance and plasmonic bowtie nanoantennas. <i>Scientific Reports</i> , 2017 , 7, 7503	4.9	10
62	A Terahertz Controlled-NOT Gate Based on Asymmetric Rotation of Polarization in Chiral Metamaterials. <i>Advanced Optical Materials</i> , 2017 , 5, 1700108	8.1	8
61	Manipulable and Hybridized, Ultralow-Threshold Lasing in a Plasmonic Laser Using Elliptical InGaN/GaN Nanorods. <i>Advanced Functional Materials</i> , 2017 , 27, 1703198	15.6	19
60	Single Photon Counting Spatial Uniformity of 4H-SiC APD Characterized by SNOM-Based Mapping System. <i>IEEE Photonics Technology Letters</i> , 2017 , 29, 1603-1606	2.2	7
59	4H-SiC Avalanche Photodiode Linear Array Operating in Geiger Mode. <i>IEEE Photonics Journal</i> , 2017 , 9, 1-7	1.8	7
58	Boosting Hot-Electron Extraction Through Deep Groove Perfect Absorber for Si-Based Photodetector. <i>IEEE Photonics Technology Letters</i> , 2017 , 29, 1884-1887	2.2	4
57	Analysis of Dark Count Mechanisms of 4H-SiC Ultraviolet Avalanche Photodiodes Working in Geiger Mode. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 4532-4539	2.9	11

56	4H-SiC SACM Avalanche Photodiode With Low Breakdown Voltage and High UV Detection Efficiency. <i>IEEE Photonics Journal</i> , 2016 , 8, 1-7	1.8	12
55	High-Brightness Polarized Green InGaN/GaN Light-Emitting Diode Structure with Al-Coated p-GaN Grating. <i>ACS Photonics</i> , 2016 , 3, 1912-1918	6.3	20
54	High Fill-Factor 4H-SiC Avalanche Photodiodes With Partial Trench Isolation. <i>IEEE Photonics Technology Letters</i> , 2016 , 28, 2526-2528	2.2	16
53	High-Performance 4H-SiC p-i-n Ultraviolet Photodiode With p Layer Formed by Al Implantation. <i>IEEE Photonics Technology Letters</i> , 2016 , 28, 1189-1192	2.2	11
52	. <i>IEEE Photonics Technology Letters</i> , 2016 , 28, 1185-1188	2.2	15
51	High-voltage photoconductive semiconductor switches fabricated on semi-insulating HVPE GaN:Fe template. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016 , 13, 374-377		4
50	Electrically tunable terahertz metamaterials with embedded large-area transparent thin-film transistor arrays. <i>Scientific Reports</i> , 2016 , 6, 23486	4.9	12
49	Polarization-independent split bull's eye antennas for infrared nano-photodetectors. <i>Scientific Reports</i> , 2016 , 6, 39106	4.9	2
48	Split Bull's Eye Antenna for High-Speed Photodetector in the Range of Visible to Mid-Infrared. <i>IEEE Photonics Technology Letters</i> , 2016 , 28, 1177-1180	2.2	7
47	Bias stress instability involving subgap state transitions in a-IGZO Schottky barrier diodes. <i>Journal Physics D: Applied Physics</i> , 2016 , 49, 395104	3	9
46	Single nanowire green InGaN/GaN light emitting diodes. <i>Nanotechnology</i> , 2016 , 27, 435205	3.4	13
45	Electrical Instability of Amorphous-Indium-Gallium-Zinc-Oxide Thin-Film Transistors under Ultraviolet Illumination. <i>Chinese Physics Letters</i> , 2016 , 33, 038502	1.8	1
44	Frequency Performance of Ring Oscillators Based on a-IGZO Thin-Film Transistors. <i>Chinese Physics Letters</i> , 2015 , 32, 047302	1.8	6
43	Study on interface characteristics in amorphous indium-gallium-zinc oxide thin-film transistors by using low-frequency noise and temperature dependent mobility measurements. <i>Solid-State Electronics</i> , 2015 , 109, 37-41	1.7	6
42	Bloch surface plasmon enhanced blue emission from InGaN/GaN light-emitting diode structures with Al-coated GaN nanorods. <i>Nanotechnology</i> , 2015 , 26, 125201	3.4	5
41	Investigation of surface-plasmon coupled red light emitting InGaN/GaN multi-quantum well with Ag nanostructures coated on GaN surface. <i>Journal of Applied Physics</i> , 2015 , 117, 153103	2.5	6
40	The Effect of Oxygen Partial Pressure during Active Layer Deposition on Bias Stability of a-InGaZnO TFTs. <i>Chinese Physics Letters</i> , 2015 , 32, 077303	1.8	
39	High-temperature and reliability performance of 4H-SiC Schottky-barrier photodiodes for UV detection. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2015 , 33, 040602	1.3	9

38	Temperature-dependent bias-stress-induced electrical instability of amorphous indium-gallium-zinc-oxide thin-film transistors. <i>Chinese Physics B</i> , 2015 , 24, 077307	1.2	3
37	Passive Quenching Electronics for Geiger Mode 4H-SiC Avalanche Photodiodes. <i>Chinese Physics Letters</i> , 2015 , 32, 128501	1.8	6
36	Demonstration of an AlGaN-based solar-blind high-voltage photoconductive switch. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2015 , 33, 040601	1.3	6
35	High-Temperature Single Photon Detection Performance of 4H-SiC Avalanche Photodiodes. <i>IEEE Photonics Technology Letters</i> , 2014 , 26, 1136-1138	2.2	44
34	Solar-blind ultraviolet band-pass filter based on metal-dielectric multilayer structures. <i>Chinese Physics B</i> , 2014 , 23, 074201	1.2	6
33	Metal-semiconductor-metal ultraviolet photodetectors directly fabricated on semi-insulating GaN:Fe template grown by hydride vapor phase epitaxy. <i>Sensors and Actuators A: Physical</i> , 2014 , 216, 308-311	3.9	4
32	Large-Swing a-IGZO Inverter With a Depletion Load Induced by Laser Annealing. <i>IEEE Electron Device Letters</i> , 2014 , 35, 1034-1036	4.4	24
31	Second-order surface-plasmon assisted responsivity enhancement in germanium nano-photodetectors with bull's eye antennas. <i>Optics Express</i> , 2014 , 22, 15949-56	3.3	9
30	Off-state breakdown and leakage current transport analysis of AlGaN/GaN high electron mobility transistors. <i>Microelectronics Reliability</i> , 2014 , 54, 2406-2409	1.2	2
29	Enhanced bias stress stability of a-InGaZnO thin film transistors by inserting an ultra-thin interfacial InGaZnO:N layer. <i>Applied Physics Letters</i> , 2013 , 102, 193505	3.4	50
28	Temperature and gate bias dependence of carrier transport mechanisms in amorphous indium-gallium-zinc oxide thin film transistors. <i>Solid-State Electronics</i> , 2013 , 86, 41-44	1.7	16
27	High Quantum Efficiency GaN-Based p-i-n Ultraviolet Photodetectors Prepared on Patterned Sapphire Substrates. <i>IEEE Photonics Technology Letters</i> , 2013 , 25, 652-654	2.2	32
26	Spectrum broadening of high-efficiency second harmonic generation in cascaded photonic crystal microcavities. <i>Optics Express</i> , 2013 , 21, 756-63	3.3	2
25	Large-scale fabrication and luminescence properties of GaN nanostructures by a soft UV-curing nanoimprint lithography. <i>Nanotechnology</i> , 2013 , 24, 405303	3.4	24
24	High Deep-Ultraviolet Quantum Efficiency GaN PIN Photodetectors with Thin P-GaN Contact Layer. <i>Chinese Physics Letters</i> , 2013 , 30, 017302	1.8	5
23	Vacuum Violet Photo-Response of AlGaN-Based Metal-Semiconductor-Metal Photodetectors. <i>Chinese Physics Letters</i> , 2013 , 30, 117301	1.8	0
22	Temperature-dependent efficiency droop behaviors of GaN-based green light-emitting diodes. <i>Chinese Physics B</i> , 2013 , 22, 047805	1.2	9
21	GaN Schottky Barrier Diodes with High-Resistivity Edge Termination Formed by Boron Implantation. <i>Chinese Physics Letters</i> , 2013 , 30, 057303	1.8	1

20	Bias-Selective Dual-Operation-Mode Ultraviolet Schottky-Barrier Photodetectors Fabricated on High-Resistivity Homoepitaxial GaN. <i>IEEE Photonics Technology Letters</i> , 2012 , 24, 2203-2205	2.2	7
19	High Quantum Efficiency Back-Illuminated AlGaIn-Based Solar-Blind Ultraviolet p-i-n Photodetectors. <i>Chinese Physics Letters</i> , 2012 , 29, 097302	1.8	14
18	Electrical instability of amorphous indium-gallium-zinc oxide thin film transistors under monochromatic light illumination. <i>Applied Physics Letters</i> , 2012 , 100, 243505	3.4	66
17	Raman probing of competitive laser heating and local recrystallization effect in ZnO nanocrystals. <i>Optics Express</i> , 2012 , 20, 23281-9	3.3	6
16	Split Bull's eye shaped aluminum antenna for plasmon-enhanced nanometer scale germanium photodetector. <i>Nano Letters</i> , 2011 , 11, 1289-93	11.5	60
15	Surface plasmon enhanced responsivity in a waveguided germanium metal-semiconductor-metal photodetector. <i>Applied Physics Letters</i> , 2010 , 97, 091102	3.4	33
14	Nanometer germanium photodetector with aluminum surface plasmon antenna for enhanced photo-response 2010 ,		2
13	Second-harmonic generation in photonic crystals with a pair of epsilon-negative and mu-negative defects. <i>Optics Express</i> , 2009 , 17, 6682-7	3.3	5
12	Raman-active Fröhlich optical phonon mode in arsenic implanted ZnO. <i>Applied Physics Letters</i> , 2009 , 94, 011913	3.4	45
11	Enhanced Vertical Light Extraction From Ultrathin Amorphous Si ₃ N ₄ Multilayers With Photonic Crystal Patterns. <i>IEEE Photonics Technology Letters</i> , 2009 , 21, 91-93	2.2	3
10	Hybridized surface plasmon polaritons at an interface between a metal and a uniaxial crystal. <i>Applied Physics Letters</i> , 2008 , 92, 141115	3.4	53
9	Physical mechanism of extraordinary electromagnetic transmission in dual-metallic grating structures. <i>Physical Review B</i> , 2008 , 78,	3.3	61
8	Strong vertical light output from thin silicon rich oxide/SiO ₂ multilayers via in-plane modulation of photonic crystal patterns. <i>Applied Physics Letters</i> , 2008 , 93, 091901	3.4	7
7	Electromagnetic transmission through one-dimensional gratings with left-handed materials. <i>Physical Review B</i> , 2007 , 75,	3.3	8
6	Controllable electromagnetic transmission based on dual-metallic grating structures composed of subwavelength slits. <i>Applied Physics Letters</i> , 2007 , 91, 111111	3.4	71
5	Low-threshold and high-efficiency optical parametric oscillator using a one-dimensional single-defect photonic crystal with quadratic nonlinearity. <i>Physical Review B</i> , 2006 , 73,	3.3	4
4	Saturation effect and forward-dominant second-harmonic generation in single-defect photonic crystals with dual localizations. <i>Optics Letters</i> , 2006 , 31, 3327-9	3	3
3	Dual localizations for second-harmonic generations using left-handed materials. <i>Applied Physics Letters</i> , 2005 , 87, 251104	3.4	3

- 2 Giant enhancement of second harmonic generation in a finite photonic crystal with a single defect and dual-localized modes. *Physical Review B*, **2004**, 70, 33 61
- 1 Electrically tunable terahertz metamaterials with embedded large-area transparent thin-film transistor arrays 1